

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Group Art Unit: 2822  
Examiner: Kiesha L. Rose  
Confirmation No.: 2321

In re PATENT APPLICATION of:

Applicant(s): Motoki KOBAYASHI et al.

Serial No.: 10/673,499

Filing Date: September 30, 2003

For: SEMICONDUCTOR DEVICE AND  
SEMICONDUCTOR DEVICE  
FABRICATION METHOD

Atty. Dkt.: FUJI 137

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) AMENDMENT  
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) in R.C.E.  
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January 10, 2006

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

This paper is in response to the Final Official Action mailed on October 19, 2005. An RCE is filed together with this Amendment. No extension fee is due. However, please charge our Deposit Account No. 18-0002 if any fees are needed to enter this paper, and please advise us accordingly. It is noted that no petition is required because of the authorization to charge, but please consider this paper a petition for extension of time if needed.

Claims 5 and 10 are canceled without prejudice to reentry and the sapphire substrate recited in those claims is now recited in base claims 1 and 6. The amendments and new claims are supported in the original claims and disclosure. In new claim 21, the "first-element area on the SOI layer" is exemplified by area Y1 in the disclosure (see Fig. 8), and the specification states that "groove G is formed in ... the first region Y1." Some changes are formal or are made for greater clarity (e.g., "lower" for "reverse" in claim 2).

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FEE ENCLOSED: \$190-  
Please charge any further  
fee to our Deposit Account  
No. 18-0002